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(54) **METHOD OF FABRICATING
SEMICONDUCTOR DEVICE**

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ABSTRACT

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The present disclosure relates to a semiconductor device and a method of fabricating the same, which includes a substrate, a plurality of bit lines, a plurality of first plugs, a first spacer, a second spacer, a plurality of second plugs and a metal silicide layer. The bit lines are disposed on the substrate. The first plugs are disposed on the substrate and separated from the bit lines. The first spacer and the second spacer are disposed between each of the bit lines and the first plugs, and include a first height and a second height respectively. The second plugs are disposed on the first plugs respectively, and the metal silicide layer is disposed between the first plugs and the second plugs, wherein an end portion of the metal silicide layer is clamped between the second spacer and the first spacer.

